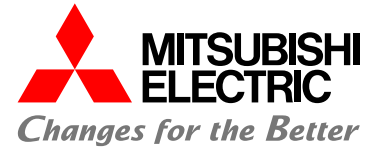


PRESS CONFERENCE



Tuesday, 9th of May 2023

PCIM Europe, Messezentrum 1
90471 Nuremberg (Germany)
NCC Ost, Ebene 3, Room Shanghai

Press Kit /
Personal Profile

PERSONAL PROFILE DR. GOURAB MAJUMDAR

Senior Fellow
Power Device Works
Mitsubishi Electric Corporation, Japan

2021 IEEE Fellow
2005 Entered IEEE-ISPSPD inaugural Hall of Fame



Academic Background

2005 Doctorate in Engineering (PhD) degree from Kyushu Institute of Technology, Japan
1977 Bachelor of Technology (B. Tech) degree in Electrical Engineering from Indian Institute of Technology (IIT), Delhi

Gourab Majumdar was born in India in June, 1955 and **acquired Japanese nationality in October, 2018.**

While his name has changed to **Gourab Suzuki**, he continues to use Gourab Majumdar as penname.

He received Bachelor of Technology degree in electrical engineering from **Indian Institute of Technology (IIT)**, Delhi, India in 1977 and Doctor of Engineering degree from Kyushu Institute of Technology (KIT), Japan in 2005.

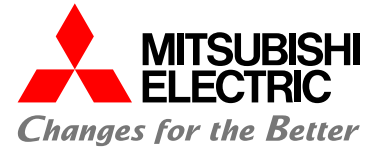
He came to Japan in September, 1978, and has been living in the country since then. **He started his job career at Mitsubishi Electric Corporation**, Japan (Mitsubishi Electric) on a special OJT program in September 1978.

He was employed by the same company in 1980 and, since 1983, has worked in its units responsible for **advanced power semiconductor development, designing and application.**

From April-2012 to March-2017, he **served as Executive Fellow**, Semiconductor & Device Group of Mitsubishi Electric. On April-2017, he was reemployed by Mitsubishi Electric on a contract basis and acted as Senior Fellow (Technology) for Semiconductor & Device Group of the same company until March-2021. From April-2022 until currently, he has been **working as Senior Fellow** for Power Device Works of Mitsubishi Electric. He has published and co-authored many technical papers and books on power semiconductor devices and holds several patents in the related fields.

He is a recipient of the prestigious **National Invention Award in Japan in 2005 for invention of the fundamental concept of IPM** (Intelligent Power Module) and has also received several other prestigious awards, including the “**Monozukuri Nihon Taishou**” (**Japan Craftsmanship Grand Prix**) award from the **Ministry of Economy, Trade and Industry** in 2013 for contribution in development and commercialization of various versions of IPM devices.

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He served as the **General Chairman of ISPSD 2013** and has been participating as a member of PCIM's Advisory Board and ISPSD's Advisory Committee. He received **IEEE-ISPSD** Contributory Award in 2017 for playing an active role in the field of Intelligent Power Module and Power IC technologies and contributing largely to the ISPSD. He was nominated to be **one of the first 32 inductees to IEEE-ISPSD Hall of Fame** for his pioneering global role in progressing IGBT and IPM technologies and was awarded the prestige in May 2018. He was promoted to IEEE Fellow in 2021. He lectured courses on advanced power semiconductor devices as a **visiting professor at Kyushu University and Tokyo Institute of Technology (TIT)** for several years till 2019. Also, he has been bestowed with **Honorary Professorship** in 2016 by **Amity University, India**.